P-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☑ Advanced trench cell design
- ☑ Low Thermal Resistance

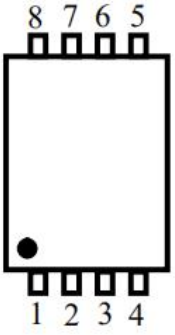
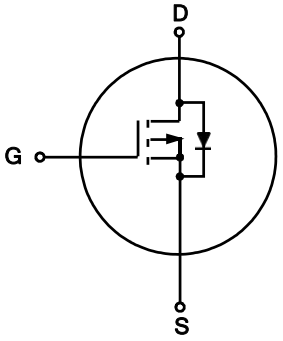
1.2 Applications

- ☑ Motor driver
- ☑ DC - DC Converter

1.3 Quick reference

- ☑ BV ≧ -100 V
- ☑ P_{tot} ≦ 35 W
- ☑ I_D ≦ - 20 A
- ☑ $R_{DS(ON)}$ ≦ 200 mΩ @ V_{GS} = - 10 V
- ☑ $R_{DS(ON)}$ ≦ 230 mΩ @ V_{GS} = - 4.5

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source		
4	Gate		
5,6,7,8	Drain		

Top View

PDFN5x6-8L

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3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	T_C = 25 ℃	-	-100	V
V_{GS}	Gate-Source Voltage	T_C = 25 ℃	-	± 20	V
I_D*	Drain Current	T_C = 25 ℃, V_{GS} = 10 V	-	-20	A
I_{DM}*,**,***	Pulsed Drain Current	T_C = 25 ℃, V_{GS} = 10 V	-	-43	A
P_{tot}*	Total Power Dissipation	T_C = 25 ℃	-	35	W
T_{stg}	Storage Temperature		- 55	150	℃
T_J	Junction Temperature		-	150	℃
I_S	Diode Forward Current	T_C = 25 ℃	-	-43	A
$R_{\theta JC}$*	Thermal Resistance- Junction to Case		-	3.5	℃ / W
$R_{\theta JA}$*	Thermal Resistance- Junction to Ambient		-	62.5	℃ / W

Notes：

* Surface Mounted on 1 in^2 pad area, t ≤ 10 sec

** Pulse width ≤ 10 μs, duty cycle ≤ 1 %

*** Limited by bonding wire

4. Marking Information

Product Name	Marking
SN20P10G	**SN20P10G YWWXXX** **X : Date Code**

5. Ordering Code

SN20P10G	Assembly Material G: Halogen and Lead Free Device

Note: NHCX defines " Green " as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

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6. Electrical Characteristics (T_C = 25 °C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_{DS} = -250 μA	-100	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_{DS} = -250 μA	-1.0	-	-2.0	V
I_{DSS}	Drain Leakage Current	V_{DS} = -80 V, V_{GS} = 0 V	-	-	-1	μA
I_{GSS}	Gate Leakage Current	V_{GS} = ± 20 V, V_{DS} = 0 V	-	-	± 100	nA
$R_{DS(ON)}$ [a]	Channel On-State Resistance	V_{GS} = -10 V, I_D = -3 A	-	170	200	mΩ
		V_{GS} = -4.5 V, I_D = -2 A	-	180	230	
Diode Characteristics						
V_{SD} [a]	Diode Forward Voltage	I_{SD} = -3 A, V_{GS} = 0 V	-	-	-1.3	V
t_{rr}	Reverse Recovery Time	I_{SD} = -3 A, dI_{SD} / dt = 100 A / μs	-	24.7	-	Ns
Q_{rr}	Reverse Recovery Charge		-	28.4	-	nC
Dynamic Characteristics [b]						
C_{iss}	Input Capacitance	V_{GS} = 0 V, V_{DS} = -50 V Frequency = 1 MHz	-	1503	-	pF
C_{oss}	Output Capacitance		-	38	-	
C_{rss}	Reverse Transfer Capacitance		-	34	-	
t_d(on)	Turn-on Delay Time	V_{DS} = - 50 V, V_{GEN} = - 10 V, R_G = 4.5 Ω, R_L = 16.6 Ω, I_{DS} = - 3 A	-	9.9	-	nS
t_r	Turn-on Rise Time		-	29.2	-	
t_d(off)	Turn-off Delay Time		-	276	-	
t_f	Turn-off Fall Time		-	84.5	-	
Gate Charge Characteristics [b]						
Q_g	Total Gate Charge	V_{GS} = - 10 V, V_{DS} = - 50 V, I_{DS} = - 3 A	-	23	-	nC
Q_{gs}	Gate-Source Charge		-	6.5	-	
Q_{gd}	Gate-Drain Charge		-	3	-	

Notes:

a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2 %

b : Guaranteed by design, not subject to production testing

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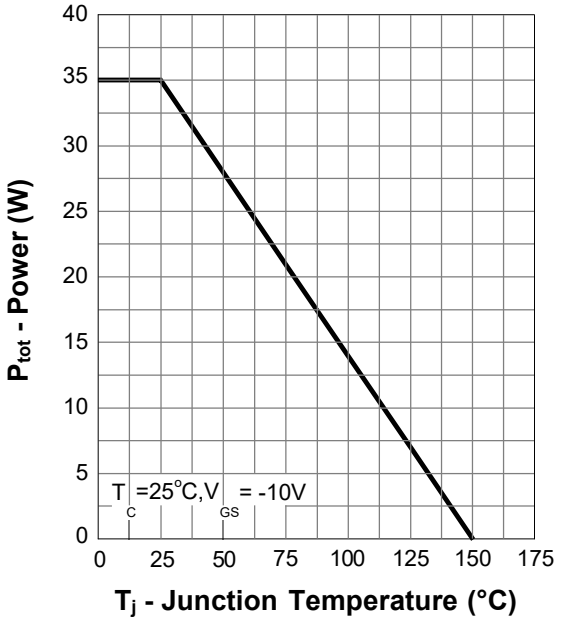
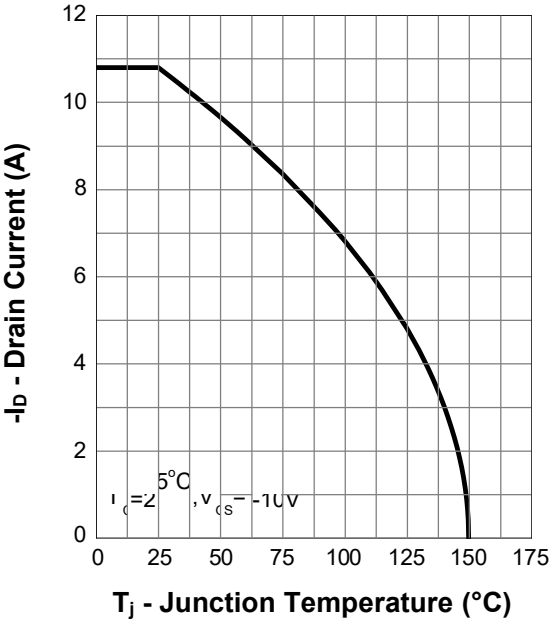
7. Typical Characteristics

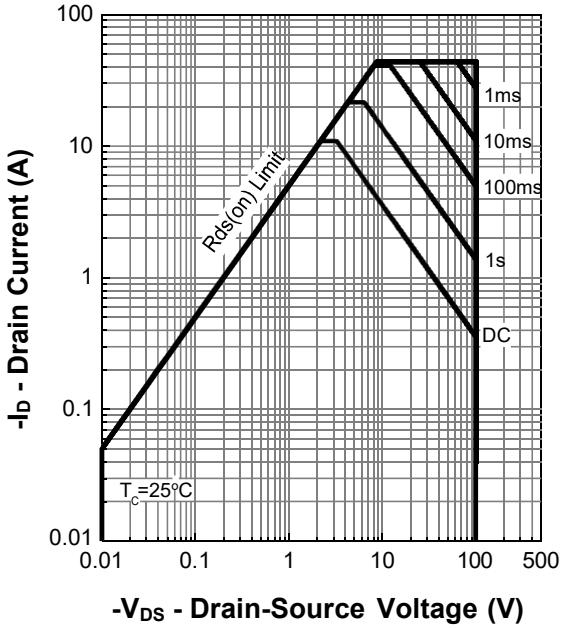
Power Capability



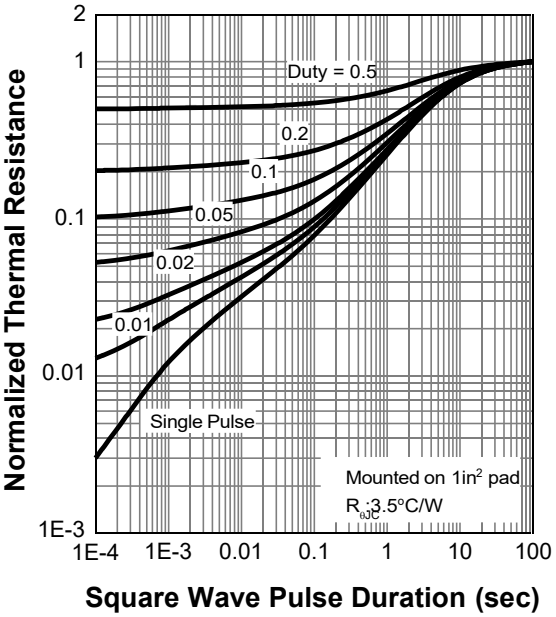
Current Capability



Safe Operation Area



Transient Thermal Impedance



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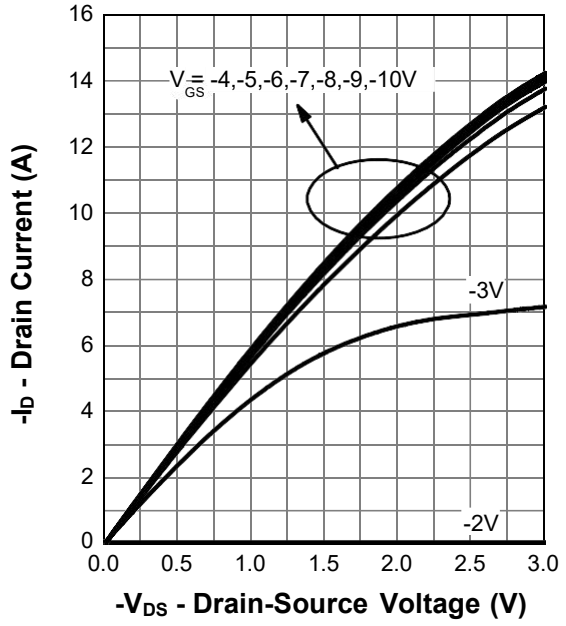
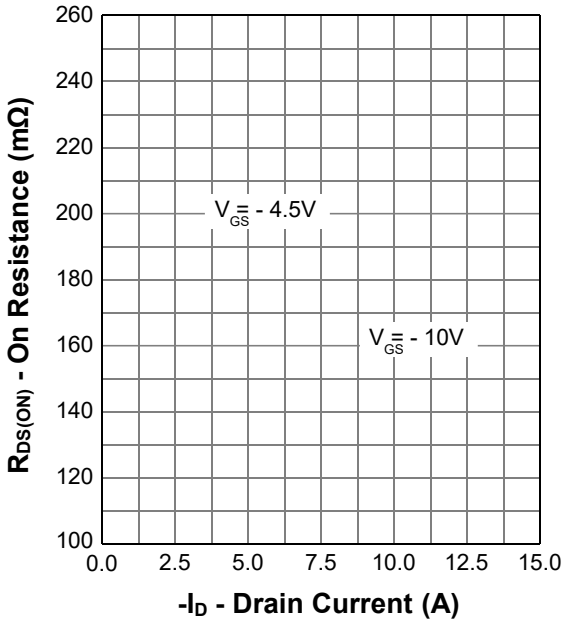
7. Typical Characteristics (cont.)

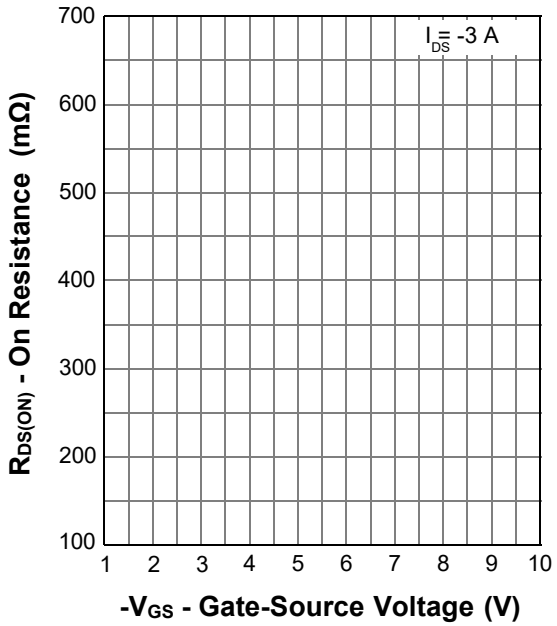
Output Characteristics



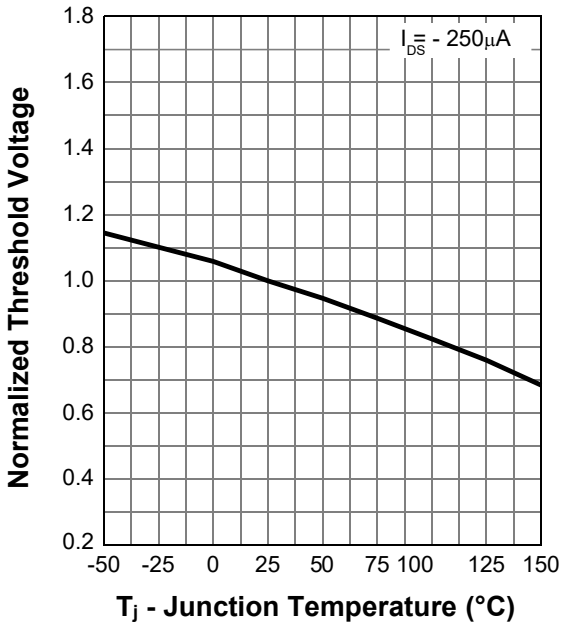
Drain-Source On Resistance



Transfer Characteristics



Normalized Threshold Voltage



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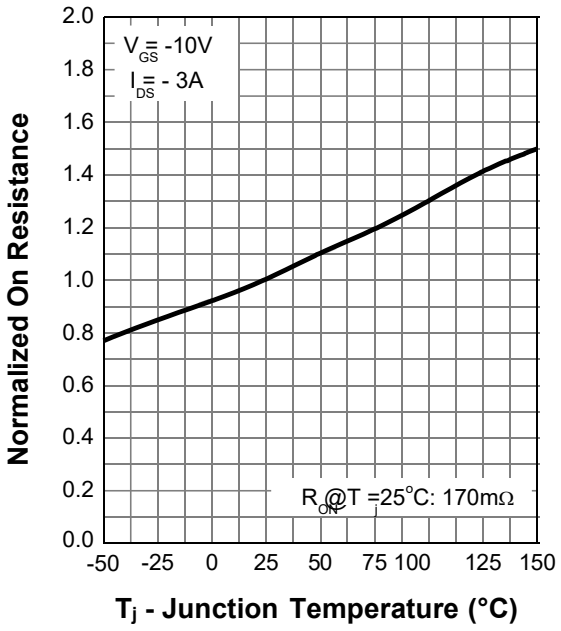
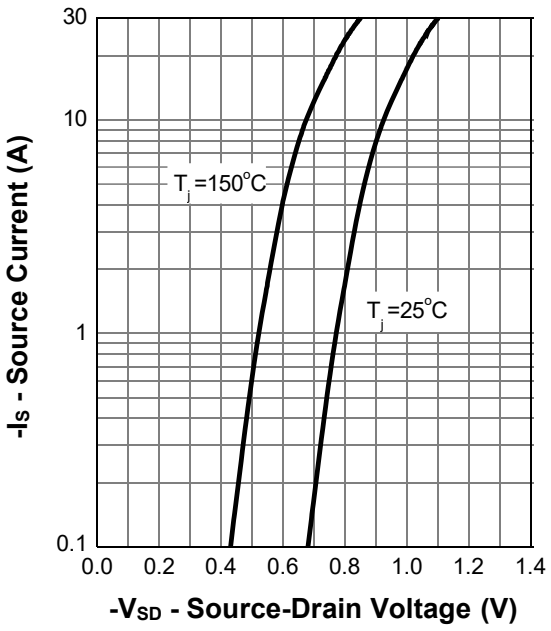
7. Typical Characteristics (cont.)

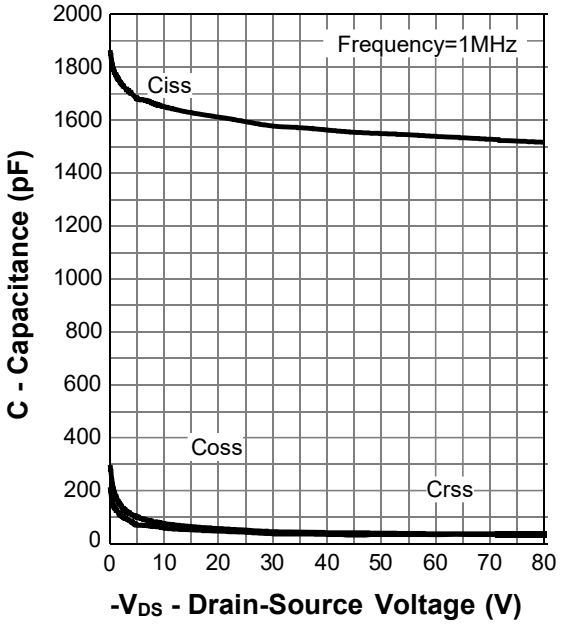
Normalized On Resistance



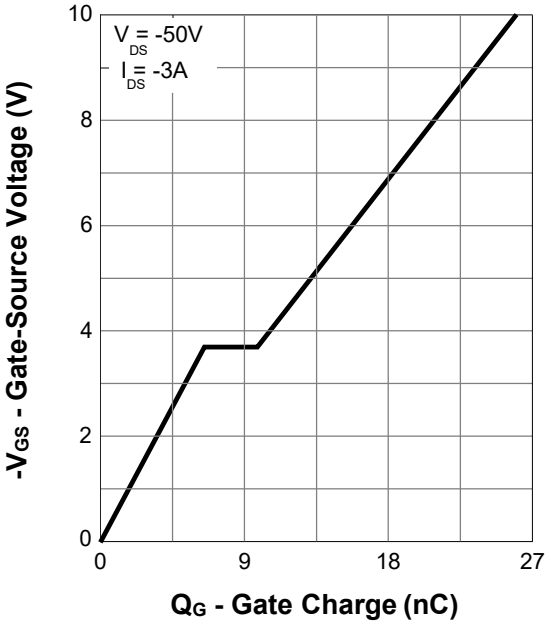
Diode Forward Current



Capacitance



Gate Charge



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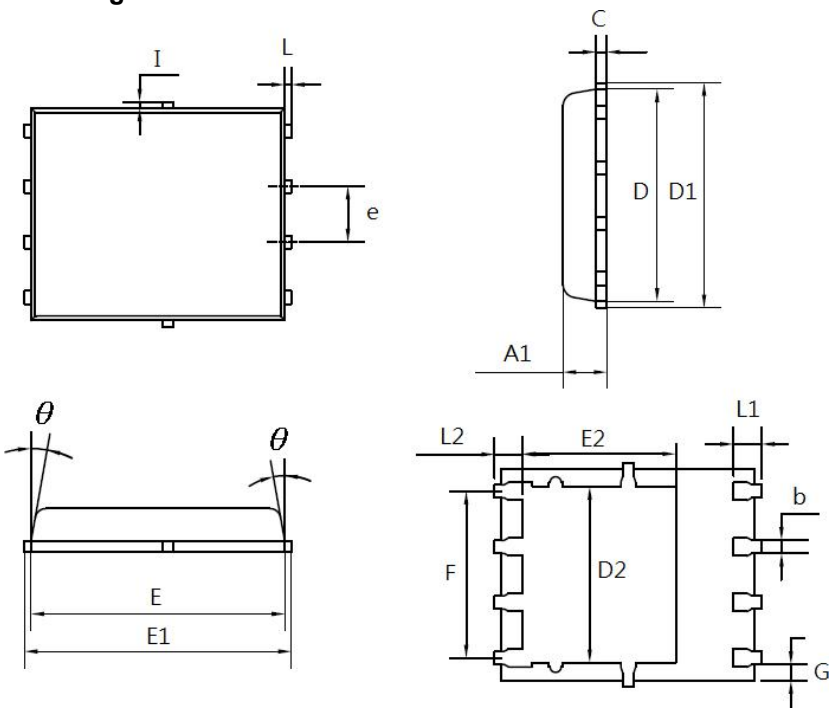
8.Package Dimensions

PDFN5x6 - 8L Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A1	0.9	1.1
b	0.2	0.4
C	0.15	0.35
D	4.7	5.1
D1	5.0	5.4
D2	4.0 BSC	
E	5.6	6.0
E1	5.9	6.3
E2	3.5 BSC	
e	1.17	1.37
F	3.61	4.01
G	0.25	0.45
I	0.05	0.25
L	0.05	0.25
L1	0.53	0.73
L2	0.63 BSC	
θ	8°	12°

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